

ABSTRACT OF THE DISCLOSURE

An N-channel transistor includes: an N-type source region, a gate electrode, a P-type body region, an N-type drain offset region, and a drain contact region, which is an N-type drain region. The transistor further includes a gate insulating film that has a thin oxide silicon film (a thin film portion) and a LOCOS film (a thick film portion). The body
5 region has an impurity profile in which the concentration reaches a maximum value near the surface and decreases with distance from the surface. The drain offset region has an impurity profile that has an impurity-concentration peak in a deep portion located a certain depth-extent below the lower face of the LOCOS film.